

# 4K × 8 Dual-Port Static RAM

### **Features**

- True dual-ported memory cells, which allow simultaneous reads of the same memory location
- 4K × 8 organization
- 0.65 micron CMOS for optimum speed and power
- High speed access: 15 ns
- Low operating power: I<sub>CC</sub> = 180 mA (max)
- Fully asynchronous operation
- Automatic power down
- Available in 52-pin plastic leaded chip carrier (PLCC)
- Pb-free packages available

### **Functional Description**

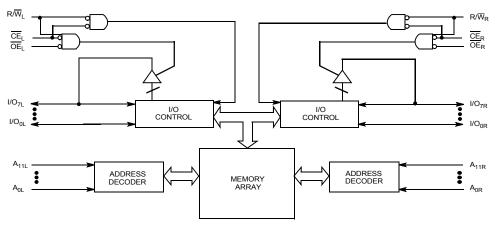
The CY7C135 is a high speed CMOS 4K × 8 dual-port static RAMs. Two ports are provided permitting independent, asynchronous access for reads and writes to any location in memory. Application areas include interprocessor/multiprocessor designs, communications status buffering, and dual-port video/graphics memory.

Each port has independent control pins:  $\underline{\text{chip}}$  enable  $(\overline{\text{CE}})$ , read or write enable ( $\overline{\text{R/W}}$ ), and output enable ( $\overline{\text{OE}}$ ). The CY7C135 is suited for those systems that do not require on-chip arbitration or are intolerant of wait states. Therefore, the user must be aware that simultaneous access to a location is possible. An automatic power down feature is controlled independently on each port by a chip enable ( $\overline{\text{CE}}$ ) pin.

The CY7C135 is available in 52-pin PLCC.

For a complete list of related documentation, click here.

## **Logic Block Diagram**





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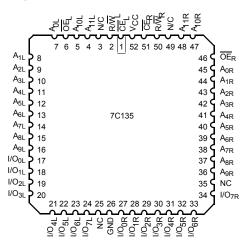


## **Selection Guide**

Parameter			Unit
Maximum access time		15	ns
Maximum operating current	Commercial	220	mA
Maximum standby current for I <sub>SB1</sub>	Commercial	60	mA

# **Pin Configurations**

Figure 1. 52-pin PLCC pinout (Top View)



## **Pin Definitions**

Left Port	Right Port	Description
A <sub>0L-11L</sub>	A <sub>0R-11R</sub>	Address lines
CEL	CE <sub>R</sub>	Chip Enable
ŌĒL	OE <sub>R</sub>	Output Enable
R/W <sub>L</sub>	R/W <sub>R</sub>	Read/Write Enable



### **Architecture**

The CY7C135 consists of an array of 4K words of 8 bits each of dual-port RAM cells, I/O and address lines, and control signals (CE, OE, R/W).

## **Functional Description**

### **Write Operation**

Data must be set up for a duration of  $t_{SD}$  before the rising edge of R/W to guarantee a valid write. Because there is no on-chip arbitration, the user must be sure that a specific location is not accessed simultaneously by both ports or erroneous data could result. A write operation is controlled by either the  $\overline{OE}$  pin (see Figure 6 on page 9) or the R/W pin (see Figure 7 on page 9). Data can be written  $t_{HZOE}$  after the  $\overline{OE}$  is deasserted or  $t_{HZWE}$  after the falling edge of R/W. Required inputs for write operations are summarized in Table 1.

If a location is being written to by one port and the opposite port attempts to read the same location, a port-to-port flowthrough delay is met before the data is valid on the output. Data is valid on the port wishing to read the location  $t_{\mbox{\scriptsize DDD}}$  after the data is presented on the writing port.

### **Read Operation**

<u>Wh</u>en reading the device, the user must assert both the  $\overline{\text{OE}}$  and  $\overline{\text{CE}}$  pins. Data is available  $t_{\text{ACE}}$  after  $\overline{\text{CE}}$  or  $t_{\text{DOE}}$  after  $\overline{\text{OE}}$  are asserted. Required inputs for read operations are summarized in Table 1.

Table 1. Non-Contending Read/Write

	Inputs			Operation	
CE	R/W	OE	I/O <sub>0</sub> –I/O <sub>7</sub>	Operation	
Н	Х	Х	High Z	Power-down	
Х	Х	Н	High Z	I/O Lines disabled	
L	Н	L	Data out	Read	
L	L	Х	Data in	Write	



## **Maximum Ratings**

Exceeding maximum ratings [1] may shorten the useful life of the device. User guidelines are not tested. Storage temperature ......-65 °C to+150 °C Ambient temperature with power applied ......–55 °C to+125 °C Supply voltage to ground potential DC voltage applied to outputs 

DC input voltage [2]	3.0 V to +7.0 V
Static discharge voltage (per MIL-STD-883, Method 3015)	> 2001 V
Latch up current	> 200 mA

## **Operating Range**

Range	Range Ambient Temperature	
Commercial	commercial 0 °C to +70 °C	
Industrial	–40 °C to +85 °C	5 V ± 10%

### **Electrical Characteristics**

Over the Operating Range

Davamatan	Description	Took Conditions	Test Conditions		7C135-15	
Parameter	Description	lest Conditions			Max	Unit
V <sub>OH</sub>	Output HIGH voltage	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA		2.4	_	V
V <sub>OL</sub>	Output LOW voltage	V <sub>CC</sub> = Min, I <sub>OL</sub> = 4.0 mA		-	0.4	V
V <sub>IH</sub>	Input HIGH voltage			2.2	_	V
V <sub>IL</sub>	Input LOW voltage			-	0.8	V
I <sub>IX</sub>	Input load current	$GND \le V_I \le V_{CC}$		-10	+10	μА
I <sub>OZ</sub>	Output leakage current	Outputs disabled, GND $\leq$ V <sub>O</sub> $\leq$ V <sub>C</sub>	С	-10	+10	μА
I <sub>CC</sub>	Operating current	V <sub>CC</sub> = Max,	Commercial	-	220	mA
		$I_{OUT} = 0 \text{ mA}$	Industrial	-	_	
I <sub>SB1</sub>	Standby current	CE <sub>L</sub> and CE <sub>R</sub> ≥ V <sub>IH</sub> ,	Commercial	-	60	mA
(Both ports TTL levels)	(Both ports TTL levels)	$f = f_{MAX}^{[3]}$	Industrial	_	_	
I <sub>SB2</sub>	Standby current	$\overline{CE}_L$ and $\overline{CE}_R \ge V_{IH}$ ,	Commercial	_	130	mA
	(One port TTL level)	$f = f_{MAX}^{[3]}$	Industrial	_	_	
I <sub>SB3</sub>	Standby current	Both ports	Commercial	_	15	mA
	(Both ports CMOS levels)	$\label{eq:center} \begin{array}{l} \overline{CE} \text{ and } \overline{CE}_R \geq V_{CC} - 0.2 \text{ V,} \\ V_{IN} \geq V_{CC} - 0.2 \text{ V or } V_{IN} \leq 0.2 \text{ V,} \\ f = 0 \ ^{[3]} \end{array}$	Industrial	-	-	
I <sub>SB4</sub>	Standby current	One port	Commercial	_	125	mA
	(One port CMOS level)	$\overline{CE}_L$ or $\overline{CE}_R \ge V_{CC} - 0.2 \text{ V}$ , $V_{IN} \ge V_{CC} - 0.2 \text{ V}$ or $V_{IN} \le 0.2 \text{ V}$ ,	Industrial	-	-	
		Active port outputs, $f = f_{MAX}^{[3]}$				

- 1. The voltage on any input or I/O pin cannot exceed the power pin during power up.
- 2. Pulse width < 20 ns.
- $f_{MAX} = 1/t_{RC}$  = All inputs cycling at f =  $1/t_{RC}$  (except output enable). f = 0 means no address or control lines change. This applies only to inputs at CMOS level standby  $I_{SB3}$ .

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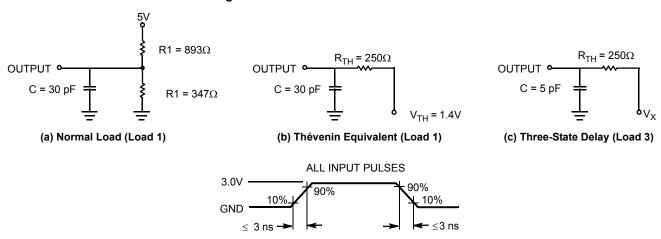


## Capacitance

Parameter [4]	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 5.0 \text{V}$	10	pF
C <sub>OUT</sub>	Output capacitance		10	pF

## **AC Test Loads and Waveforms**

Figure 2. AC Test Loads and Waveforms



### Note

Tested initially and after any design or process changes that may affect these parameters.



## **Switching Characteristics**

Over the Operating Range

Parameter [5]	Post total	7C1:	35-15	
Parameter [9]	Description		Max	Unit
Read Cycle			•	
t <sub>RC</sub>	Read cycle time	15	_	ns
t <sub>AA</sub>	Address to data valid	-	15	ns
t <sub>OHA</sub>	Output hold from address change	3	-	ns
t <sub>ACE</sub>	CE LOW to data valid	_	15	ns
t <sub>DOE</sub>	OE LOW to data valid	_	10	ns
t <sub>LZOE</sub> <sup>[6, 7, 8]</sup>	OE Low to Low Z	3	-	ns
t <sub>HZOE</sub> [6, 7, 8]	OE HIGH to High Z	-	10	ns
t <sub>I ZCF</sub> [6, 7, 8]	CE LOW to Low Z	3	-	ns
t <sub>HZCE</sub> <sup>[6, 7, 8]</sup>	CE HIGH to High Z	-	10	ns
t <sub>PU</sub> <sup>[8]</sup>	CE LOW to Power-up	0	-	ns
t <sub>PD</sub> <sup>[8]</sup>	CE HIGH to Power-down	_	15	ns
Write Cycle				
t <sub>WC</sub>	Write cycle time	15	-	ns
t <sub>SCE</sub>	CE LOW to Write End	12	-	ns
t <sub>AW</sub>	Address setup to Write End	12	-	ns
t <sub>HA</sub>	Address hold from Write End	2	-	ns
t <sub>SA</sub>	Address setup to Write Start	0	-	ns
t <sub>PWE</sub>	Write pulse width	12	-	ns
t <sub>SD</sub>	Data setup to Write End		-	ns
t <sub>HD</sub>	Data hold from Write End		_	ns
t <sub>HZWE</sub> <sup>[7, 8]</sup>	R/W LOW to High Z		10	ns
t <sub>LZWE</sub> [7, 8]	R/W HIGH to Low Z 3		_	ns
t <sub>WDD</sub> <sup>[9]</sup>	Write pulse to data delay	_	30	ns
t <sub>DDD</sub> <sup>[9]</sup>	Write data valid to read data valid	_	25	ns

### Notes

<sup>5.</sup> Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and 30 pF load capacitance.

<sup>6.</sup> At any given temperature and voltage condition for any given device,  $t_{HZCE}$  is less than  $t_{LZCE}$  and  $t_{HZOE}$  is less than  $t_{LZCE}$ .

<sup>7.</sup> Test conditions used are Load 3.

<sup>8.</sup> This parameter is guaranteed but not tested.

<sup>9.</sup> For information on port-to-port delay through RAM cells from writing port to reading port, refer to Figure 5 on page 8.



## **Switching Waveforms**

Figure 3. Read Cycle No. 1 [10, 11]

### Either Port Address Access

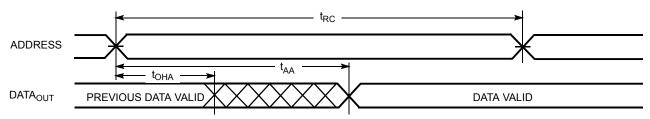


Figure 4. Read Cycle No. 2 [10, 12]

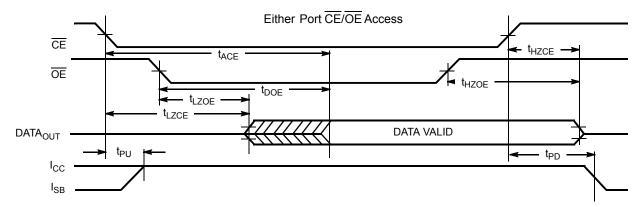
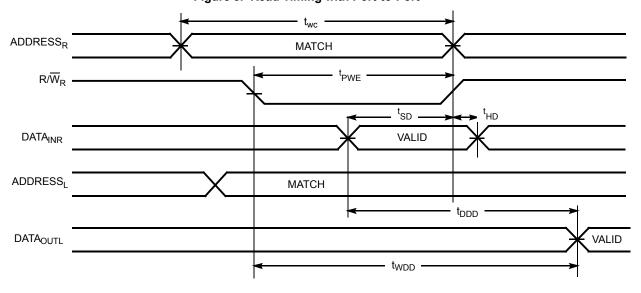


Figure 5. Read Timing with Port-to-Port [13]



- 10. R/W is HIGH for read cycle.

  11. Device is continuously selected,  $\overline{CE} = V_{|L}$  and  $\overline{OE} = V_{|L}$ .

  12. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.

  13.  $\overline{CE}_L = \overline{CE}_R = LOW$ ; R/W<sub>L</sub> = HIGH.



## Switching Waveforms (continued)

Figure 6. Write Cycle No. 1: OE Three-States Data I/Os (Either Port) [14, 15, 16]

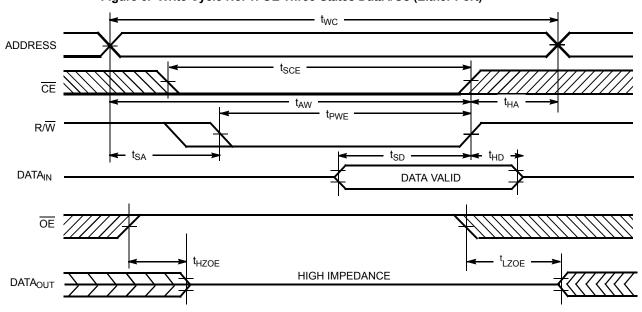
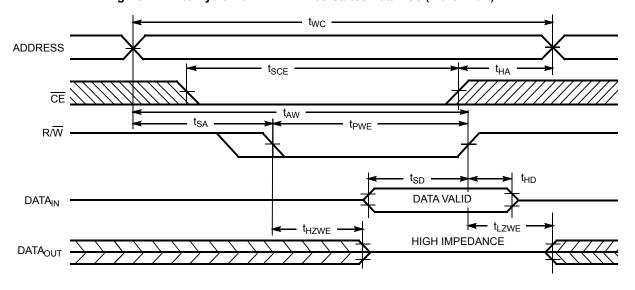


Figure 7. Write Cycle No. 2: R/W Three-States Data I/Os (Either Port) [15, 17]



### Notes

<sup>14.</sup> The internal write time of the memory is defined by the overlap of CE and R/W LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write.

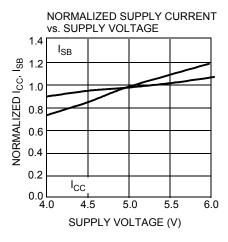
<sup>15.</sup> R/W must be HIGH during all address transactions.

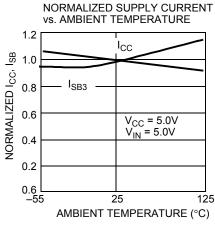
16. If OE is LOW during a R/W controlled write cycle, the write pulse width must be the larger of t<sub>PWE</sub> or (t<sub>HZWE</sub> + t<sub>SD</sub>) to allow the I/O drivers to turn off and data to be placed on the bus for the required t<sub>SD</sub>. If OE is HIGH during a R/W controlled write cycle (as in this example), this requirement does not apply and the write pulse can be as short as the specified t<sub>PWE</sub>.

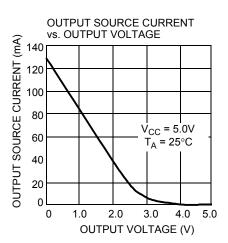
17. Data I/O pins enter high impedance when OE is held LOW during write.

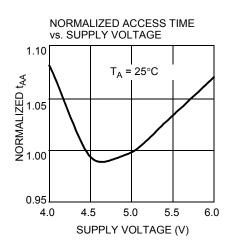


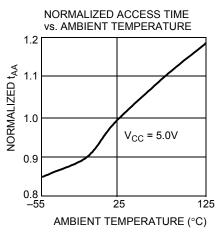
## **Typical DC and AC Characteristics**

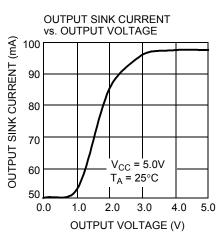


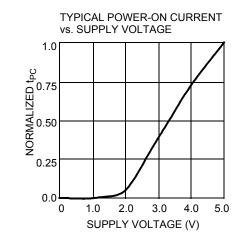


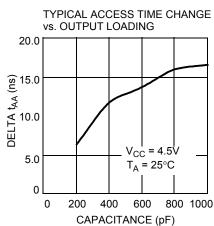


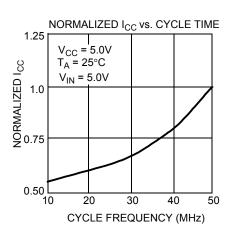












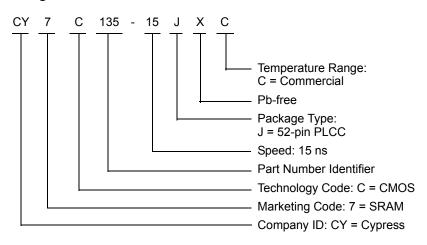


## **Ordering Information**

### 4K × 8 Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY7C135-15JXC	51-85004	52-pin PLCC (Pb-free)	Commercial

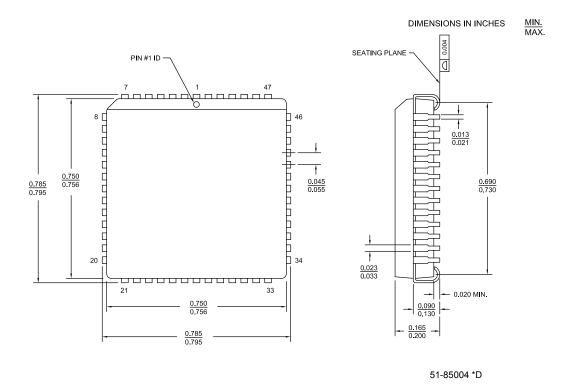
## **Ordering Code Definitions**





# **Package Diagram**

Figure 8. 52-pin PLCC (0.756 × 0.756 Inches) J52 Package Outline, 51-85004



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# **Acronyms**

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
PLCC	Plastic Leaded Chip Carrier
SRAM	Static Random Access Memory
TQFP	Thin Quad Flat Pack

## **Document Conventions**

## **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μA	microampere			
mA	milliampere			
mV	millivolt			
ns	nanosecond			
Ω	ohm			
pF	picofarad			
V	volt			
W	watt			



# **Document History Page**

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	110181	SZV	10/21/01	Change from Spec number: 38-00541 to 38-06038
*A	122288	RBI	12/27/02	Updated Maximum Ratings: Added Power up requirements (Added Note 1 and referred the same in maximum ratings).
*B	236763	YDT	SEE ECN	Updated Features: Removed "Pin-compatible and functionally equivalent to IDT7134/IDT71342"
*C	393413	YIM	See ECN	Added Pb-free Logo. Updated Ordering Information: Added Pb-free parts (CY7C135-15JXC, CY7C135-25JXC).
*D	2623540	VKN / PYRS	12/17/08	Updated Ordering Information: Added CY7C135A parts. Removed CY7C1342 from the ordering information table.
*E	2897217	RAME	03/22/2010	Updated Ordering Information. Updated Package Diagram.
*F	3081925	ADMU	11/10/2010	Added Ordering Code Definitions under Ordering Information. Added Acronyms and Units of Measure. Updated to new template
*G	3805117	SMCH	11/07/2012	Updated Document Title to read as "CY7C135, 4 K × 8 Dual-Port Static RAM" Updated Features (Changed value of I <sub>CC</sub> from 160 mA to 180 mA, removed CY7C1342 related information).  Updated Functional Description (Removed CY7C135A, CY7C1342 related information, removed the Note "CY7C135 and CY7C135A are functionally identical" and its reference).  Updated Logic Block Diagram (Removed Semaphore Arbitration (related to CY7C1342)).  Updated Selection Guide (Removed CY7C135A, CY7C1342 related information, removed 20 ns, 35 ns, 55 ns speed bins related information).  Updated Pin Configurations (Removed CY7C135A, CY7C1342 related information).  Updated Pin Definitions (Removed SEM (related to CY7C1342)).  Updated Architecture (Removed CY7C135A, CY7C1342 related information).  Updated Functional Description (Updated Read Operation (Removed CY7C1342 related information), removed Semaphore Operation, updated Table 1 (Removed CY7C1342 related information), removed the table "Semaphore Operation Example").  Updated Electrical Characteristics (Removed CY7C135A, CY7C1342 related information, removed 20 ns speed bin related information).  Removed Electrical Characteristics (Corresponding to CY7C135 and CY7C1342 with 35 ns, 55 ns speed bins).  Updated Switching Characteristics (Removed CY7C135A, CY7C1342 related information, removed 20 ns, 35 ns, 55 ns speed bins related information, removed the Note "Semaphore timing applies only to CY7C1342." and its reference).  Updated Switching Waveforms (Removed CY7C135A, CY7C1342 related information).
*H	4202909	SMCH	11/26/2013	Updated Ordering Information (Updated part numbers). Updated Package Diagram: spec 51-85004 – Changed revision from *C to *D. Updated to new template. Completing Sunset Review.



# **Document History Page (continued)**

Document Title: CY7C135, 4K × 8 Dual-Port Static RAM Document Number: 38-06038							
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change			
*	4264122	SMCH	01/27/2014	Removed 25 ns speed bin related information across the document.			
*J	4580622	SMCH	11/26/2014	Updated Functional Description: Added "For a complete list of related documentation, click here." at the end.			
*K	5506734	NILE	11/04/2016	Updated Ordering Information: No change in part numbers. Removed column "Package Name". Added a column "Package Diagram". Updated to new template. Completing Sunset Review.			



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